

Product Overview

NGTB35N65FL2: IGBT, 650V 35A FS2 Solar/UPS

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- $5\mu s$ Short-Circuit Capability

Applications

- Solar Inverters
- Uninterruptible Power Supplies (UPS)
- Welding

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{GE}^{(sa)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Packaged Diode	Package Type
NGTB35N65FL2WG	Pb-free Halide free	Active	650	35	1.7	2.2	0.28	0.84	68	7	125	5	-	300	Yes	TO-247-3

For more information please contact your local sales support at www.onsemi.com.

Created on: 1/16/2019